

DRV8840 直流电机驱动器 IC

1 特性

- 单路 H 桥电流控制电机驱动器
- 8.2V 至 45V 宽工作电源电压范围
- 五位电流控制支持多达 32 个电流电平
- 低 MOSFET $R_{DS(on)}$ 典型值为 0.4Ω (HS + LS)
- 24V、 $T_A = 25^\circ\text{C}$ 下的最大驱动电流为 5A
- 内置 3.3V 基准输出
- 并行数字控制接口
- 热增强型表面贴装封装
- 保护特性：
 - 过流保护 (OCP)
 - 热关断 (TSD)
 - VM 欠压锁定 (UVLO)
 - 故障条件指示引脚 (nFAULT)

2 应用

- 打印机
- 扫描仪
- 办公自动化设备
- 游戏机
- 工厂自动化
- 机器人技术

3 说明

DRV8840 可为打印机、扫描仪以及其它自动化设备应用提供集成电机驱动器解决方案。该器件具有一个 H 桥驱动器，可驱动一个 DC 电机。每个输出驱动器块包含被配置为全 H 桥的 N 通道功率 MOSFET 以驱动电机绕组。DRV8840 可提供最高 5A 的峰值电流或 3.5A 的输出电流（在 24V 和 25°C 下，散热正常）。

一个简单的并行数字控制接口与行业标准器件兼容。可对衰减模式进行设定，以便在被禁用时实现电机制动或缓动。

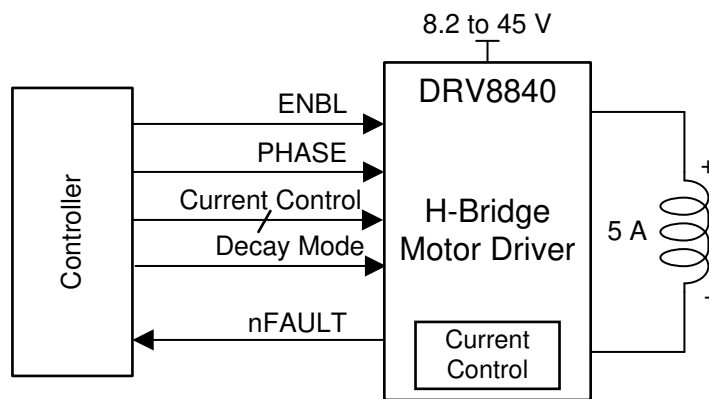
还提供了用于过流保护、短路保护、欠压锁定和过热保护的内部关断功能。

DRV8840 采用带 PowerPAD™ 的 28 引脚 HTSSOP 封装（环保：RoHS，无镉/溴）。

器件信息(1)

器件型号	封装	封装尺寸 (标称值)
DRV8840	HTSSOP (28)	9.70mm × 4.40mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。



简化版原理图



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4 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision D (December 2015) to Revision E (March 2023)	Page
• 更正了拼写错误.....	1

Changes from Revision C (August 2013) to Revision D (December 2015)	Page
• 添加了引脚配置和功能部分、ESD 等级表、特性说明部分、器件功能模式、应用和实施部分、电源相关建议部分、布局部分、器件和文档支持部分以及机械、封装和可订购信息部分.....	1
• 更新了特性要点.....	1
• Added MIN value for ISENSEx row from - 0.3 V to - 0.8 V	5

5 Pin Configuration and Functions

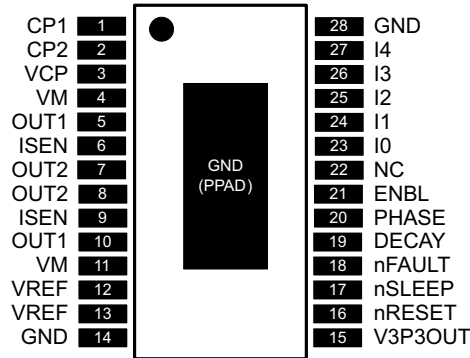


图 5-1. PWP Package 28-Pin HTSSOP Top View

表 5-1. Pin Functions

PIN		I/O ⁽¹⁾	DESCRIPTION	EXTERNAL COMPONENTS OR CONNECTIONS
NAME	NO.			
POWER AND GROUND				
GND	14, 28	—	Device ground	
VM	4, 11	—	Bridge A power supply	Connect to motor supply (8.2 - 45 V). Both pins must be connected to same supply.
V3P3OUT	15	O	3.3-V regulator output	Bypass to GND with a 0.47- μ F, 6.3-V ceramic capacitor. Can be used to supply VREF.
CP1	1	IO	Charge pump flying capacitor	Connect a 0.01- μ F 50-V capacitor between CP1 and CP2.
CP2	2	IO	Charge pump flying capacitor	
VCP	3	IO	High-side gate drive voltage	Connect a 0.1- μ F 16-V ceramic capacitor and a 1-M Ω resistor to VM.
CONTROL				
PHASE	20	I	Bridge phase (direction)	Logic high sets OUT1 high, OUT2 low. Internal pulldown.
ENBL	21	I	Bridge enable	Logic high to enable H-bridge. Internal pulldown.
I0	23	I	Current set inputs	Sets winding current as a percentage of full-scale. Internal pulldown.
I1	24	I		
I2	25	I		
I3	26	I		
I4	27	I		
DECAY	19	I	Decay (brake) mode	Low = brake (slow decay), high = coast (fast decay). Internal pulldown and pullup.
nRESET	16	I	Reset input	Active-low reset input initializes the logic and disables the H-bridge outputs. Internal pulldown.
nSLEEP	17	I	Sleep mode input	Logic high to enable device, logic low to enter low-power sleep mode. Internal pulldown.
VREF	12,13	I	Current set reference input	Reference voltage for winding current set. Both pins must be connected together on the PCB.

表 5-1. Pin Functions (continued)

PIN		I/O ⁽¹⁾	DESCRIPTION	EXTERNAL COMPONENTS OR CONNECTIONS
NAME	NO.			
STATUS				
nFAULT	18	OD	Fault	Logic low when in fault condition (overtemperature, overcurrent)
OUTPUT				
ISEN	6, 9	IO	Bridge ground / Isense	Connect to current sense resistor. Both pins must be connected together on the PCB.
OUT1	5, 10	O	Bridge output 1	Connect to motor winding. Both pins must be connected together on the PCB.
OUT2	7, 8	O	Bridge output 2	Connect to motor winding. Both pins must be connected together on the PCB.

(1) Directions: I = input, O = output, OZ = tri-state output, OD = open-drain output, IO = input/output

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)^{(1) (2)}

		MIN	MAX	UNIT
VMx	Power supply voltage	- 0.3	47	V
	Digital pin voltage	- 0.5	7	V
VREF	Input voltage	- 0.3	4	V
	ISENSEx pin voltage ⁽³⁾	- 0.8	0.8	V
	Peak motor drive output current, $t < 1 \mu\text{S}$	Internally limited		A
	Continuous motor drive output current ⁽⁴⁾	0	5	A
	Continuous total power dissipation	See # 6.4		
T _J	Operating virtual junction temperature	- 40	150	°C
T _A	Operating ambient temperature	- 40	85	°C
T _{stg}	Storage temperature	- 60	150	°C

- (1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under # 6.3 is not implied. Exposure to absolute - maximum - rated conditions for extended periods may affect device reliability.
- (2) All voltage values are with respect to network ground pin.
- (3) Transients of ± 1 V for less than 25 ns are acceptable.
- (4) Power dissipation and thermal limits must be observed.

6.2 ESD Ratings

		VALUE	UNIT
V _(ESD)	Electrostatic discharge		
	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins ⁽¹⁾	±2000	V
Charged device model (CDM), per JEDEC specification JESD22-C101, all pins ⁽²⁾	±500		

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V _M	Motor power supply voltage ⁽¹⁾	8.2	45	V
V _{REF}	VREF input voltage ⁽²⁾	1	3.5	V
I _{V3P3}	V3P3OUT load current	0	1	mA
f _{PWM}	Externally applied PWM frequency	0	100	kHz

- (1) All V_M pins must be connected to the same supply voltage.
- (2) Operational at VREF between 0 V and 1 V, but accuracy is degraded.

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		DRV8840	UNIT
		PWP (HTSSOP)	
		28 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	31.6	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	15.9	°C/W
R _{θJB}	Junction-to-board thermal resistance	5.6	°C/W
ψ _{JT}	Junction-to-top characterization parameter	0.2	°C/W
ψ _{JB}	Junction-to-board characterization parameter	5.5	°C/W

THERMAL METRIC ⁽¹⁾		DRV8840	UNIT
		PWP (HTSSOP)	
		28 PINS	
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	1.4	°C/W

- (1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, [SPRA953](#).

6.5 Electrical Characteristics

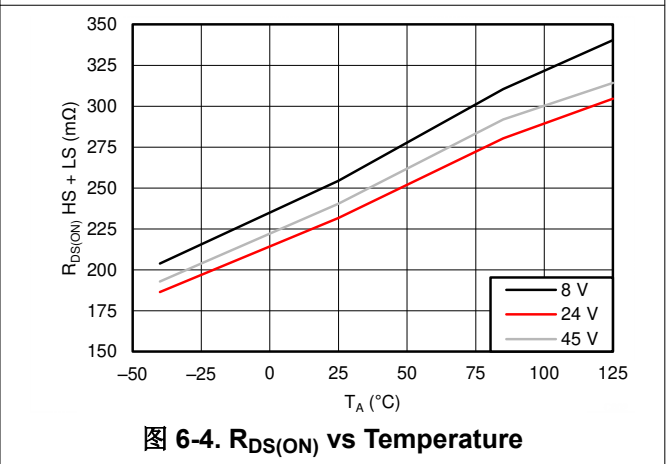
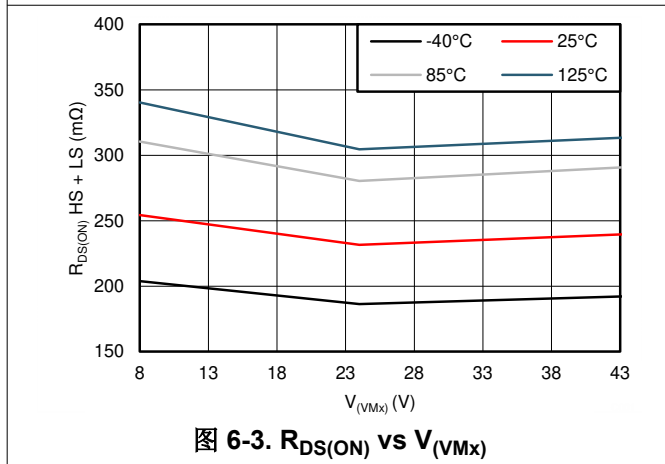
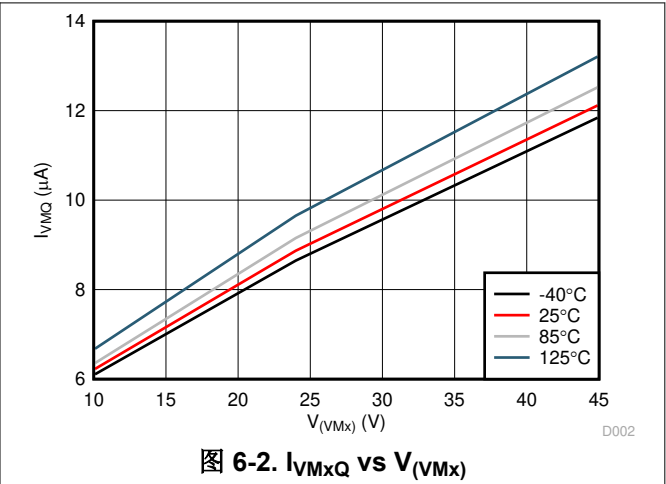
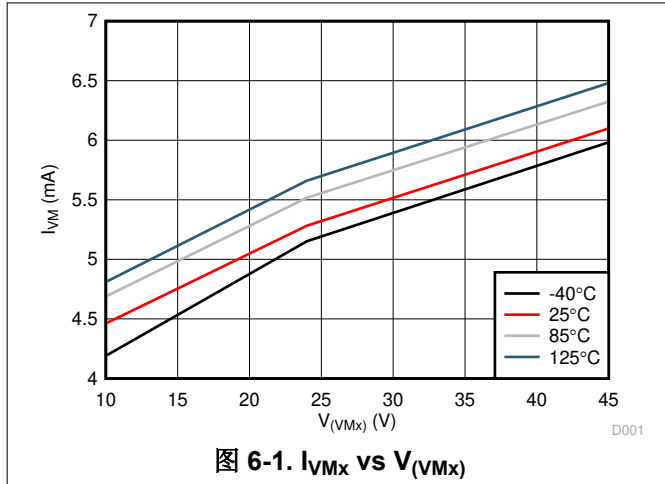
over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
POWER SUPPLIES						
I_{VM}	VM operating supply current	$V_M = 24\text{ V}$, $f_{PWM} < 50\text{ kHz}$		5	8	mA
I_{VMQ}	VM sleep mode supply current	$V_M = 24\text{ V}$		10	20	$\mu\text{ A}$
V_{UVLO}	VM undervoltage lockout voltage	V_M rising		7.8	8.2	V
V3P3OUT REGULATOR						
V_{3P3}	V3P3OUT voltage	$I_{OUT} = 0$ to 1 mA	3.2	3.3	3.4	V
LOGIC-LEVEL INPUTS						
V_{IL}	Input low voltage			0.6	0.7	V
V_{IH}	Input high voltage		2.2		5.25	V
V_{HYS}	Input hysteresis		0.3	0.45	0.6	V
I_{IL}	Input low current	$V_{IN} = 0$	-20		20	$\mu\text{ A}$
I_{IH}	Input high current	$V_{IN} = 3.3\text{ V}$		33	100	$\mu\text{ A}$
R_{PD}	Internal pulldown resistance			100		k Ω
nFAULT OUTPUT (OPEN-DRAIN OUTPUT)						
V_{OL}	Output low voltage	$I_O = 5\text{ mA}$			0.5	V
I_{OH}	Output high leakage current	$V_O = 3.3\text{ V}$			1	$\mu\text{ A}$
DECAY INPUT						
V_{IL}	Input low threshold voltage	For slow decay (brake) mode	0		0.8	V
V_{IH}	Input high threshold voltage	For fast decay (coast) mode	2			V
I_{IN}	Input current				± 40	$\mu\text{ A}$
R_{PU}	Internal pullup resistance			130		k Ω
R_{PD}	Internal pulldown resistance			80		k Ω
H-BRIDGE FETS						
$R_{DS(ON)}$	HS FET on resistance	$V_M = 24\text{ V}$, $I_O = 1\text{ A}$, $T_J = 25^\circ\text{C}$		0.1		Ω
		$V_M = 24\text{ V}$, $I_O = 1\text{ A}$, $T_J = 85^\circ\text{C}$		0.13	0.16	
$R_{DS(ON)}$	LS FET on resistance	$V_M = 24\text{ V}$, $I_O = 1\text{ A}$, $T_J = 25^\circ\text{C}$		0.1		Ω
		$V_M = 24\text{ V}$, $I_O = 1\text{ A}$, $T_J = 85^\circ\text{C}$		0.13	0.16	
I_{OFF}	Off-state leakage current		-40		40	$\mu\text{ A}$
MOTOR DRIVER						
f_{PWM}	Internal current control PWM frequency			50		kHz
t_{BLANK}	Current sense blanking time			3.75		$\mu\text{ s}$
t_R	Rise time		30		200	ns
t_F	Fall time		30		200	ns
PROTECTION CIRCUITS						
I_{OCP}	Overcurrent protection trip level		6			A
t_{TSD}	Thermal shutdown temperature	Die temperature	150	160	180	$^\circ\text{C}$
CURRENT CONTROL						
I_{REF}	VREF input current	$V_{REF} = 3.3\text{ V}$	-3		3	$\mu\text{ A}$
V_{TRIP}	ISENSE trip voltage	$V_{REF} = 3.3\text{ V}$, 100% current setting	635	660	685	mV

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
ΔI_{TRIP} Current trip accuracy (relative to programmed value)	VREF = 3.3 V, 5% current setting	- 25%		25%	
	VREF = 3.3 V, 10% - 34% current setting	- 15%		15%	
	VREF = 3.3 V, 38% - 67% current setting	- 10%		10%	
	VREF = 3.3 V, 71% - 100% current setting	- 5%		5%	
A_{ISENSE} Current sense amplifier gain	Reference only		5		V/V

6.6 Typical Characteristics



7 Detailed Description

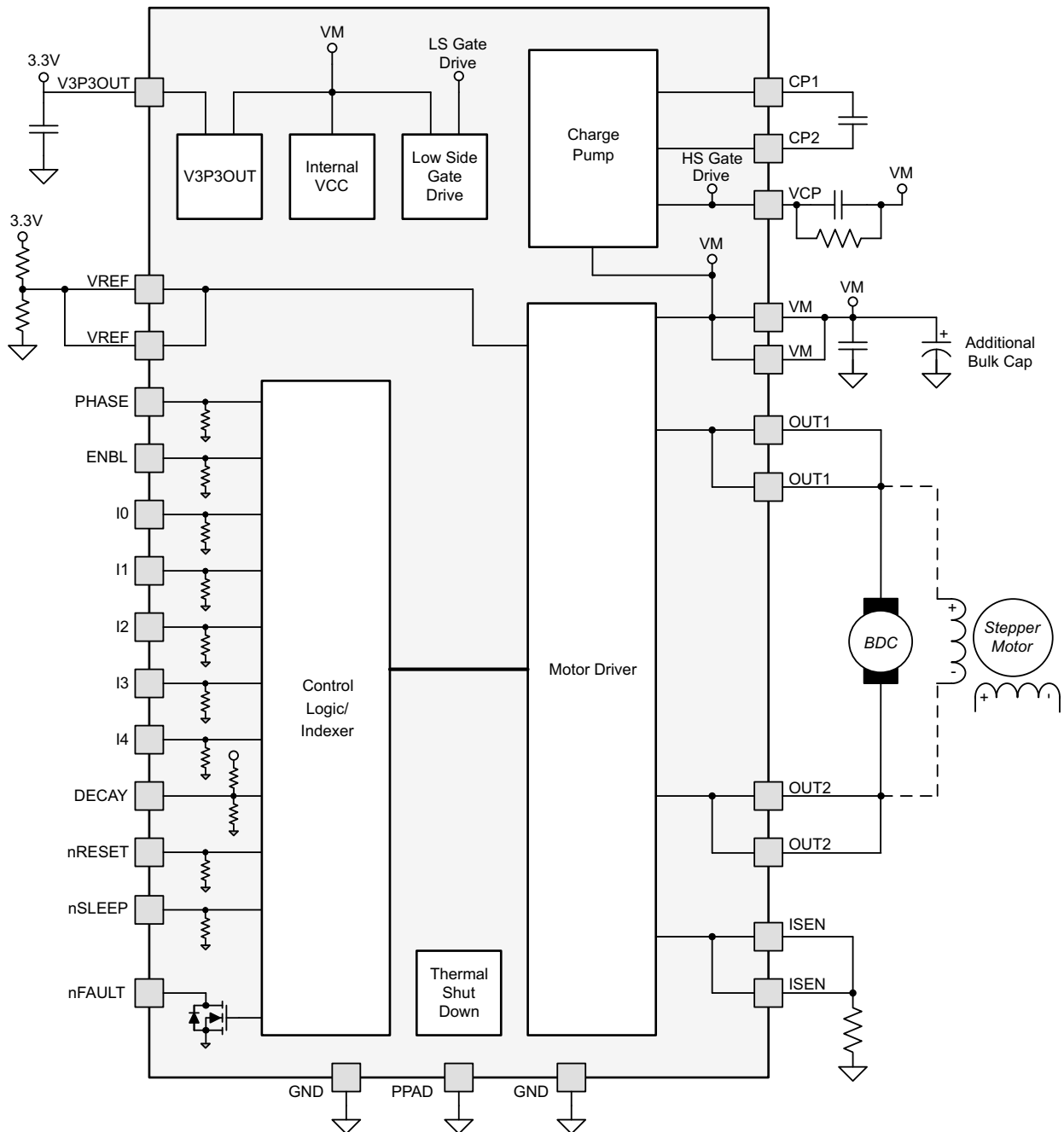
7.1 Overview

The DRV8840 is an integrated motor driver solution for printers, scanners, and other automated equipment applications. The device integrates a single NMOS H-bridge, charge pump, current sense, current regulation, and device protection circuitry. The DRV8828 can be powered from a single voltage supply from 8.2 V to 45 V, and is capable of providing a continuous output current up to 5 A.

A simple PHASE/ENBL interface allows for easy interfacing to an external controller. A 5 bit current control scheme allows for up to 32 discrete current levels. The current regulation method is adjustable between slow and fast decay.

Integrated protection circuits allows the device to monitor and protect against overcurrent, undervoltage, and overtemperature faults which are all reported through a fault indication pin (nFAULT). A low power sleep mode is integrated which allows the system to lower power consumption when not driving the motor.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 PWM Motor Driver

The DRV8840 device contains one H-bridge motor driver with current-control PWM circuitry. A block diagram of the motor control circuitry is shown in [Figure 7-1](#).

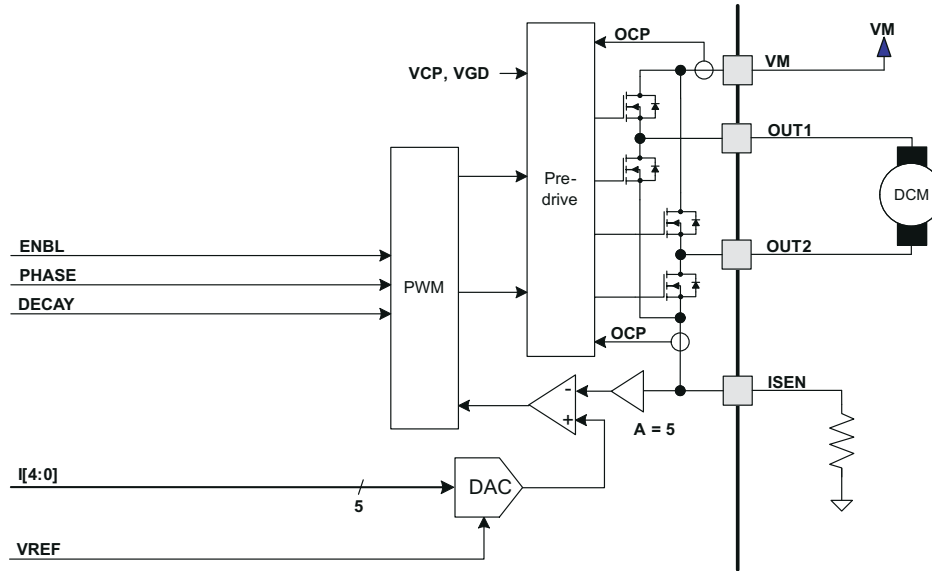


图 7-1. Motor Control Circuitry

There are multiple VM, ISEN, OUT, and VREF pins. All like-named pins must be connected together on the PCB.

7.3.2 Bridge Control

The PHASE input pin controls the direction of current flow through the H-bridge, and hence the direction of rotation of a DC motor. The ENBL input pin enables the H-bridge outputs when active high, and can also be used for PWM speed control of the motor. Note that the state of the DECAY pin selects the behavior of the bridge when ENBL = 0, allowing the selection of slow decay (brake) or fast decay (coast). 表 7-1 shows the logic.

表 7-1. H-Bridge Logic

DECAY	ENBL	PHASE	OUT1	OUT2
0	0	X	L	L
1	0	X	Z	Z
X	1	1	H	L
X	1	0	L	H

The control inputs have internal pulldown resistors of approximately 100 k Ω .

7.3.3 Current Regulation

The maximum current through the motor winding is regulated by a fixed-frequency PWM current regulation, or current chopping. When the H-bridge is enabled, current rises through the winding at a rate dependent on the DC voltage and inductance of the winding. Once the current hits the current chopping threshold, the bridge disables the current until the beginning of the next PWM cycle.

For DC motors, current regulation is used to limit the start-up and stall current of the motor. Speed control is typically performed by providing an external PWM signal to the ENBLx input pins.

If the current regulation feature is not needed, it can be disabled by connecting the ISENSE pins directly to ground and the VREF pins to V3P3.

The PWM chopping current is set by a comparator which compares the voltage across a current sense resistor connected to the ISEN pin, multiplied by a factor of 5, with a reference voltage. The reference voltage is input from the VREF pin, and is scaled by a 5-bit DAC that allows current settings of zero to 100% in an approximately sinusoidal sequence.

The full-scale (100%) chopping current is calculated in [方程式 1](#).

$$I_{\text{CHOP}} = \frac{V_{\text{REFX}}}{5 \times R_{\text{ISENSE}}} \quad (1)$$

Example:

If a 0.25-Ω sense resistor is used and the VREFx pin is 2.5 V, the full-scale (100%) chopping current will be 2.5 V / (5 × 0.25 Ω) = 2 A.

Five input pins (I0 - I4) are used to scale the current in the bridge as a percentage of the full-scale current set by the VREF input pin and sense resistance. The I0 - I4 pins have internal pulldown resistors of approximately 100 kΩ. The function of the pins is shown in [表 7-2](#).

表 7-2. Pin Functions

I[4..0]	RELATIVE CURRENT (% FULL-SCALE CHOPPING CURRENT)
0x00h	0%
0x01h	5%
0x02h	10%
0x03h	15%
0x04h	20%
0x05h	24%
0x06h	29%
0x07h	34%
0x08h	38%
0x09h	43%
0x0Ah	47%
0x0Bh	51%
0x0Ch	56%
0x0Dh	60%
0x0Eh	63%
0x0Fh	67%
0x10h	71%
0x11h	74%
0x12h	77%
0x13h	80%
0x14h	83%
0x15h	86%
0x16h	88%
0x17h	90%
0x18h	92%
0x19h	94%
0x1Ah	96%
0x1Bh	97%
0x1Ch	98%
0x1Dh	99%
0x1Eh	100%
0x1Fh	100%

7.3.4 Decay Mode and Braking

During PWM current chopping, the H-bridge is enabled to drive current through the motor winding until the PWM current chopping threshold is reached. This is shown in 图 7-2 as case 1. The current flow direction shown indicates the state when the xENBL pin is high.

Once the chopping current threshold is reached, the H-bridge can operate in two different states, fast decay or slow decay.

In fast decay mode, once the PWM chopping current level has been reached, the H-bridge reverses state to allow winding current to flow in a reverse direction. As the winding current approaches zero, the bridge is disabled to prevent any reverse current flow. Fast decay mode is shown in 图 7-2 as case 2.

In slow decay mode, winding current is re-circulated by enabling both of the low-side FETs in the bridge. This is shown in 图 7-2 as case 3.

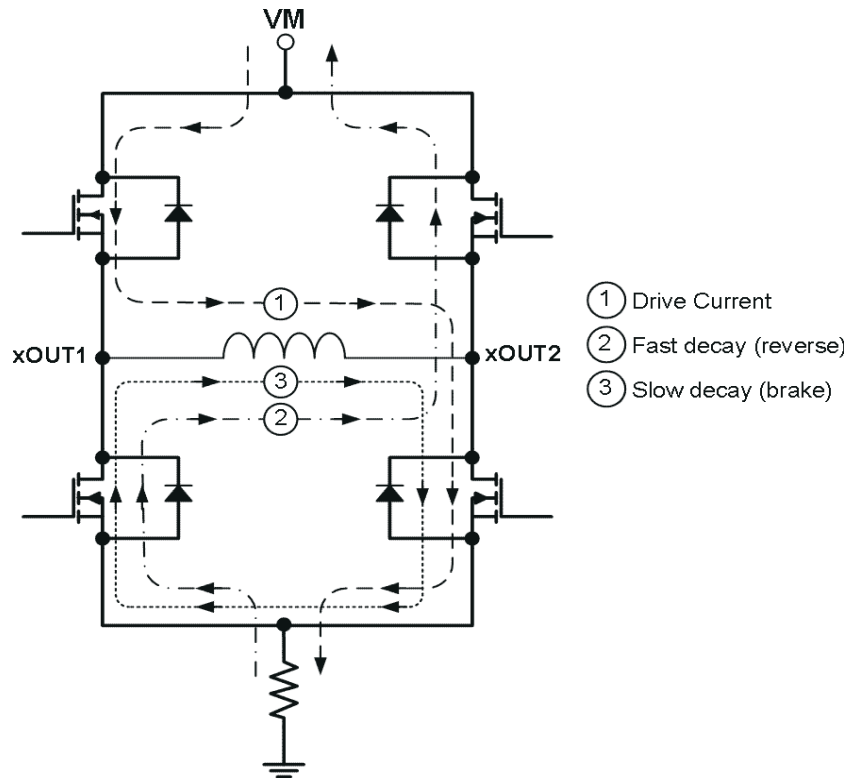


图 7-2. Decay Mode

The DRV8840 device supports fast decay and slow decay mode. Slow or fast decay mode is selected by the state of the DECAY pin - logic low selects slow decay, and logic high sets fast decay mode. The DECAY pin has both an internal pullup resistor of approximately 130 k Ω and an internal pulldown resistor of approximately 80 k Ω . This sets the mixed decay mode if the pin is left open or undriven.

DECAY mode also affects the operation of the bridge when it is disabled (by taking the ENBL pin inactive). This applies if the ENABLE input is being used for PWM speed control of the motor, or if it is simply being used to start and stop motor rotation.

If the DECAY pin is high (fast decay), when the bridge is disabled fast decay mode will be entered until the current through the bridge reaches zero. Once the current is at zero, the bridge is disabled to prevent the motor from reversing direction. This allows the motor to coast to a stop.

If the DECAY pin is low (slow decay), both low-side FETs will be turned on when ENBL is made inactive. This essentially shorts out the back EMF of the motor, causing the motor to brake, and stop quickly. The low-side FETs will stay in the ON state even after the current reaches zero.

7.3.5 Blanking Time

After the current is enabled in an H-bridge, the voltage on the xISEN pin is ignored for a fixed period of time before enabling the current sense circuitry. This blanking time is fixed at 3.75 μ s. Note that the blanking time also sets the minimum on time of the PWM.

7.3.6 Protection Circuits

The DRV8840 device is fully protected against undervoltage, overcurrent and overtemperature events.

7.3.6.1 Overcurrent Protection (OCP)

An analog current limit circuit on each FET limits the current through the FET by removing the gate drive. If this analog current limit persists for longer than the OCP time, all FETs in the H-bridge will be disabled and the nFAULT pin will be driven low. The device will remain disabled until either nRESET pin is applied, or VM is removed and re-applied.

Overcurrent conditions on both high and low side devices; i.e., a short to ground, supply, or across the motor winding will all result in an overcurrent shutdown. Note that overcurrent protection does not use the current sense circuitry used for PWM current control, and is independent of the I_{SENSE} resistor value or VREF voltage.

7.3.6.2 Thermal Shutdown (TSD)

If the die temperature exceeds safe limits, all FETs in the H-bridge will be disabled and the nFAULT pin will be driven low. Once the die temperature has fallen to a safe level operation will automatically resume.

7.3.6.3 Undervoltage Lockout (UVLO)

If at any time the voltage on the VM pins falls below the undervoltage lockout threshold voltage, all circuitry in the device will be disabled and internal logic will be reset. Operation will resume when V_M rises above the UVLO threshold.

7.4 Device Functional Modes

7.4.1 nRESET and nSLEEP Operation

The nRESET pin, when driven active low, resets the internal logic. It also disables the H-bridge driver. All inputs are ignored while nRESET is active.

Driving nSLEEP low will put the device into a low power sleep state. In this state, the H-bridges are disabled, the gate drive charge pump is stopped, the V3P3OUT regulator is disabled, and all internal clocks are stopped. In this state all inputs are ignored until nSLEEP returns inactive high. When returning from sleep mode, some time (approximately 1 ms) needs to pass before the motor driver becomes fully operational. Note that nRESET and nSLEEP have internal pulldown resistors of approximately 100 k Ω . These signals need to be driven to logic high for device operation.

8.2.1 Design Requirements

表 8-1 shows the design parameters for this application.

表 8-1. Design Parameters

DESIGN PARAMETER	REFERENCE	EXAMPLE VALUE
Supply Voltage	VM	24 V
Motor Winding Resistance	RM	3.9 V
Motor Winding Inductance	LM	2.9 mH
Target Chopping Current	ITRIP	1.5 A
Sense Resistor	RSENSE	100 mΩ
VREF Voltage	VREF	0.75 V

8.2.2 Detailed Design Procedure

8.2.2.1 Current Regulation

The maximum current (I_{TRIP}) is set by the Ix pins, the VREF analog voltage, and the sense resistor value (R_{SENSE}). When starting a brushed DC motor, a large inrush current may occur because there is no back-EMF and high detent torque. Current regulation will act to limit this inrush current and prevent high current on start-up.

$$I_{TRIP} / (5 \times R_{SENSE}) \quad (2)$$

Example: If the desired chopping current is 1.5 A:

- Set $R_{SENSE} = 100 \text{ m}\Omega$
- VREF would have to be 0.75 V
- Create a resistor divider network from V3P3OUT (3.3 V) to set $V_{REF} = 0.75 \text{ V}$
- Set $R_2 = 10 \text{ k}\Omega$ and set $R_1 = 3 \text{ k}\Omega$

8.2.2.2 Sense Resistor

For optimal performance, it is important for the sense resistor to be:

- Surface-mount
- Low inductance
- Rated for high enough power
- Placed closely to the motor driver

The power dissipated by the sense resistor equals $I_{rms}^2 \times R$. For example, if the RMS motor current is 1.5 A and a 200-mΩ sense resistor is used, the resistor will dissipate $1.5 \text{ A}^2 \times 0.2 \Omega = 0.3 \text{ W}$. The power quickly increases with greater current levels.

Resistors typically have a rated power within some ambient temperature range, along with a de-rated power curve for high ambient temperatures. When a PCB is shared with other components generating heat, margin should be added. It is always best to measure the actual sense resistor temperature in a final system, along with the power MOSFETs, as those are often the hottest components.

Because power resistors are larger and more expensive than standard resistors, it is common practice to use multiple standard resistors in parallel, between the sense node and ground. This distributes the current and heat dissipation.

8.2.3 Application Curves

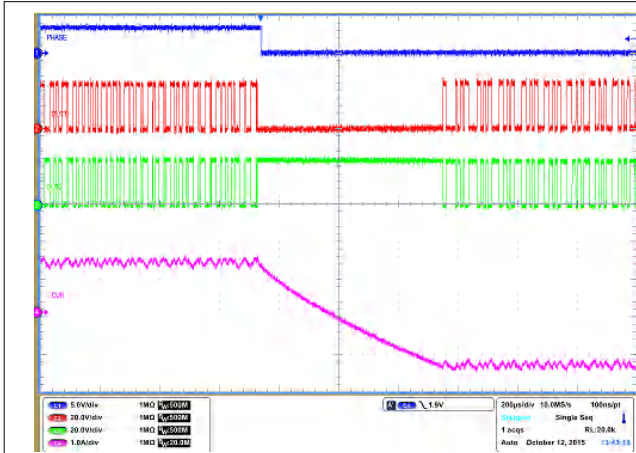


图 8-2. DRV8842 Current Regulation

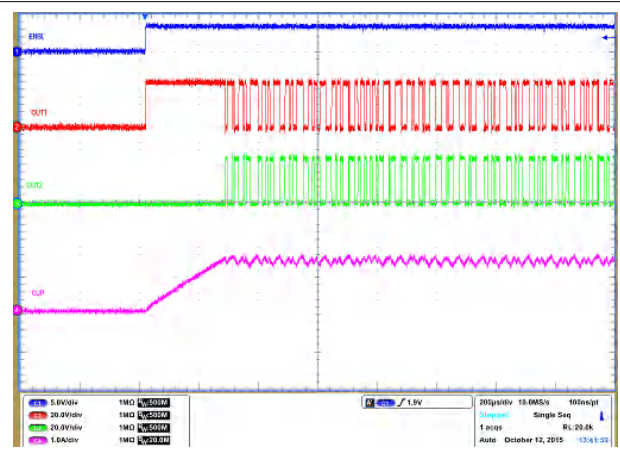


图 8-3. DRV8842 Direction Change

9 Power Supply Recommendations

The DRV8840 is designed to operate from an input voltage supply (VM) range from 8.2 V to 45 V. The device has an absolute maximum rating of 47 V. A 0.1- μ F ceramic capacitor rated for VM must be placed at each VM pin as close to the DRV8840 as possible. In addition, a bulk capacitor must be included on VM.

9.1 Bulk Capacitance Sizing

Having appropriate local bulk capacitance is an important factor in motor drive system design. It is generally beneficial to have more bulk capacitance, while the disadvantages are increased cost and physical size.

The amount of local capacitance needed depends on a variety of factors, including:

- The highest current required by the motor system.
- The power supply's capacitance and ability to source current.
- The amount of parasitic inductance between the power supply and motor system.
- The acceptable voltage ripple.
- The type of motor used (Brushed DC, Brushless DC, Stepper).
- The motor braking method.

The inductance between the power supply and motor drive system will limit the rate current can change from the power supply. If the local bulk capacitance is too small, the system will respond to excessive current demands or dumps from the motor with a change in voltage. When adequate bulk capacitance is used, the motor voltage remains stable and high current can be quickly supplied.

The data sheet generally provides a recommended value, but system-level testing is required to determine the appropriate sized bulk capacitor.

The voltage rating for bulk capacitors should be greater than the operating voltage, to provide margin for cases when the motor transfers energy to the supply.

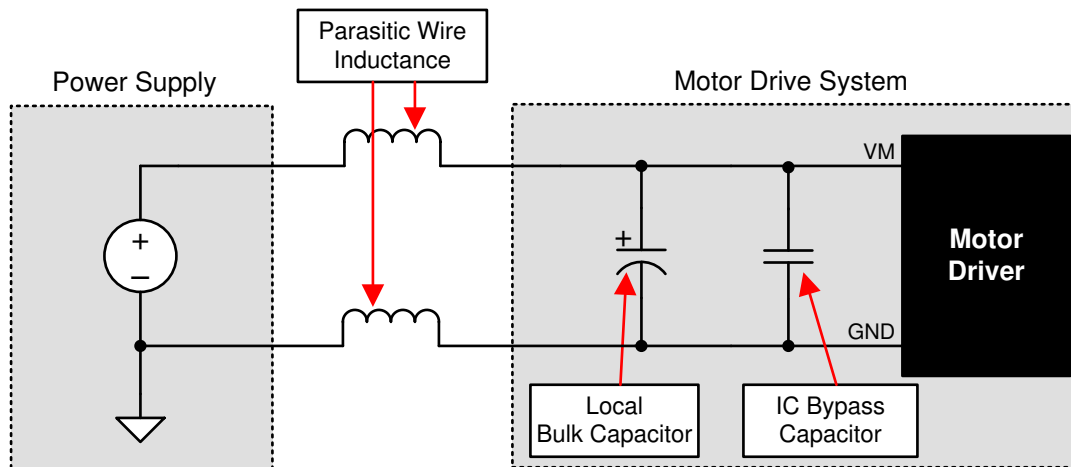


图 9-1. Setup of Motor Drive System With External Power Supply

10 Layout

10.1 Layout Guidelines

Each VM terminal must be bypassed to GND using a low-ESR ceramic bypass capacitors with recommended values of 0.1 μF rated for VM. These capacitors should be placed as close to the VM pins as possible with a thick trace or ground plane connection to the device GND pin.

The VM pin must be bypassed to ground using a bulk capacitor rated for VM. This component may be an electrolytic.

A low-ESR ceramic capacitor must be placed in between the CP1 and CP2 pins. TI recommends a value of 0.1 μF rated for VM. Place this component as close to the pins as possible.

A low-ESR ceramic capacitor must be placed in between the VM and VCP pins. TI recommends a value of 0.47 μF rated for 16 V. Place this component as close to the pins as possible. In addition, place a 1 M Ω between VM and VCP.

Bypass V3P3OUT to ground with a ceramic capacitor rated 6.3 V. Place this bypassing capacitor as close to the pin as possible.

The current sense resistor should be placed as close as possible to the device pins to minimize trace inductance between the pin and resistor.

10.2 Layout Example

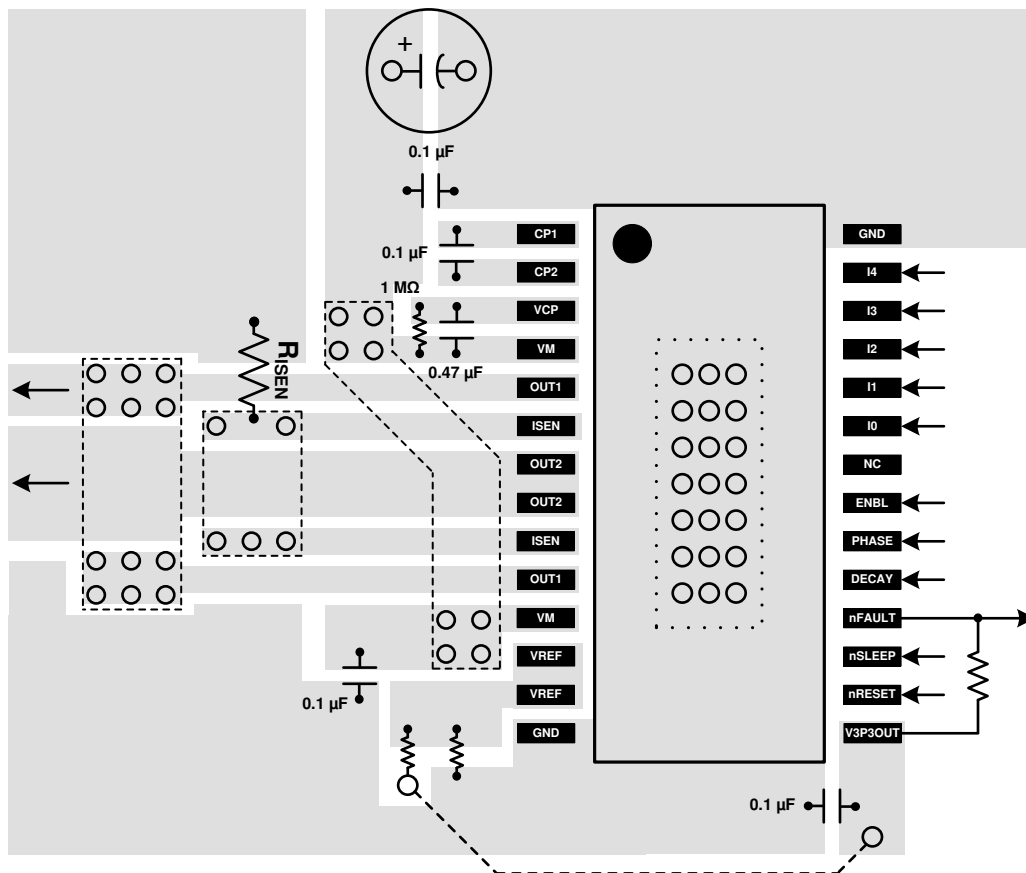


图 10-1. Example Layout

10.3 Thermal Considerations

The DRV8840 has thermal shutdown (TSD) as described above. If the die temperature exceeds approximately 150°C, the device will be disabled until the temperature drops to a safe level.

Any tendency of the device to enter TSD is an indication of either excessive power dissipation, insufficient heatsinking, or too high an ambient temperature.

10.3.1 Power Dissipation

Average power dissipation in the DRV8840 when running a DC motor can be roughly estimated by: [方程式 3](#).

$$P = 2 \times R_{DS(ON)} \times (I_{OUT})^2 \quad (3)$$

where

- P is the power dissipation of one H-bridge
- $R_{DS(ON)}$ is the resistance of each FET
- I_{OUT} is the RMS output current being applied to each winding.

I_{OUT} is equal to the average current drawn by the DC motor. Note that at start-up and fault conditions this current is much higher than normal running current; these peak currents and their duration also need to be taken into consideration. The factor of 2 comes from the fact that at any instant two FETs are conducting winding current (one high-side and one low-side).

The maximum amount of power that can be dissipated in the device is dependent on ambient temperature and heatsinking.

Note that $R_{DS(ON)}$ increases with temperature, so as the device heats, the power dissipation increases. This must be taken into consideration when sizing the heatsink.

10.3.2 Heatsinking

The PowerPAD™ package uses an exposed pad to remove heat from the device. For proper operation, this pad must be thermally connected to copper on the PCB to dissipate heat. On a multilayer PCB with a ground plane, this can be accomplished by adding a number of vias to connect the thermal pad to the ground plane. On PCBs without internal planes, copper area can be added on either side of the PCB to dissipate heat. If the copper area is on the opposite side of the PCB from the device, thermal vias are used to transfer the heat between top and bottom layers.

For details about how to design the PCB, see the TI application report, *PowerPAD™ Thermally Enhanced Package (SLMA002)*, and the TI application brief, *PowerPAD™ Made Easy (SLMA004)*, available at www.ti.com.

In general, the more copper area that can be provided, the more power can be dissipated.

11 Device and Documentation Support

11.1 Documentation Support

11.1.1 Related Documentation

For related documentation see the following:

- *PowerPAD™ Thermally Enhanced Package*, [SLMA002](#)
- *PowerPAD™ Made Easy*, [SLMA004](#)

11.2 Community Resources

11.3 Trademarks

PowerPAD™ is a trademark of Texas Instruments.
所有商标均为其各自所有者的财产。

12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
DRV8840PWP	ACTIVE	HTSSOP	PWP	28	50	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 85	DRV8840	Samples
DRV8840PWPR	ACTIVE	HTSSOP	PWP	28	2000	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 85	DRV8840	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
DRV8840PWPR	HTSSOP	PWP	28	2000	330.0	16.4	6.9	10.2	1.8	12.0	16.0	Q1

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
DRV8840PWPR	HTSSOP	PWP	28	2000	350.0	350.0	43.0

TUBE


*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
DRV8840PWP	PWP	HTSSOP	28	50	530	10.2	3600	3.5

GENERIC PACKAGE VIEW

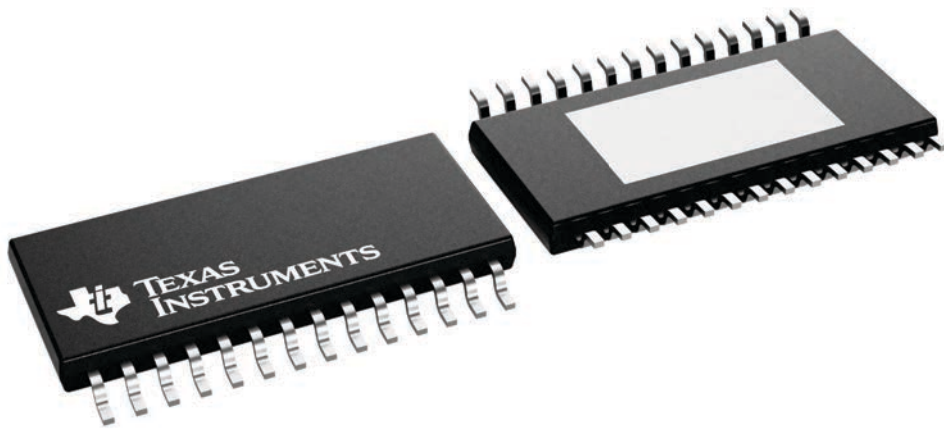
PWP 28

PowerPAD™ TSSOP - 1.2 mm max height

4.4 x 9.7, 0.65 mm pitch

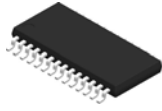
SMALL OUTLINE PACKAGE

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



4224765/B

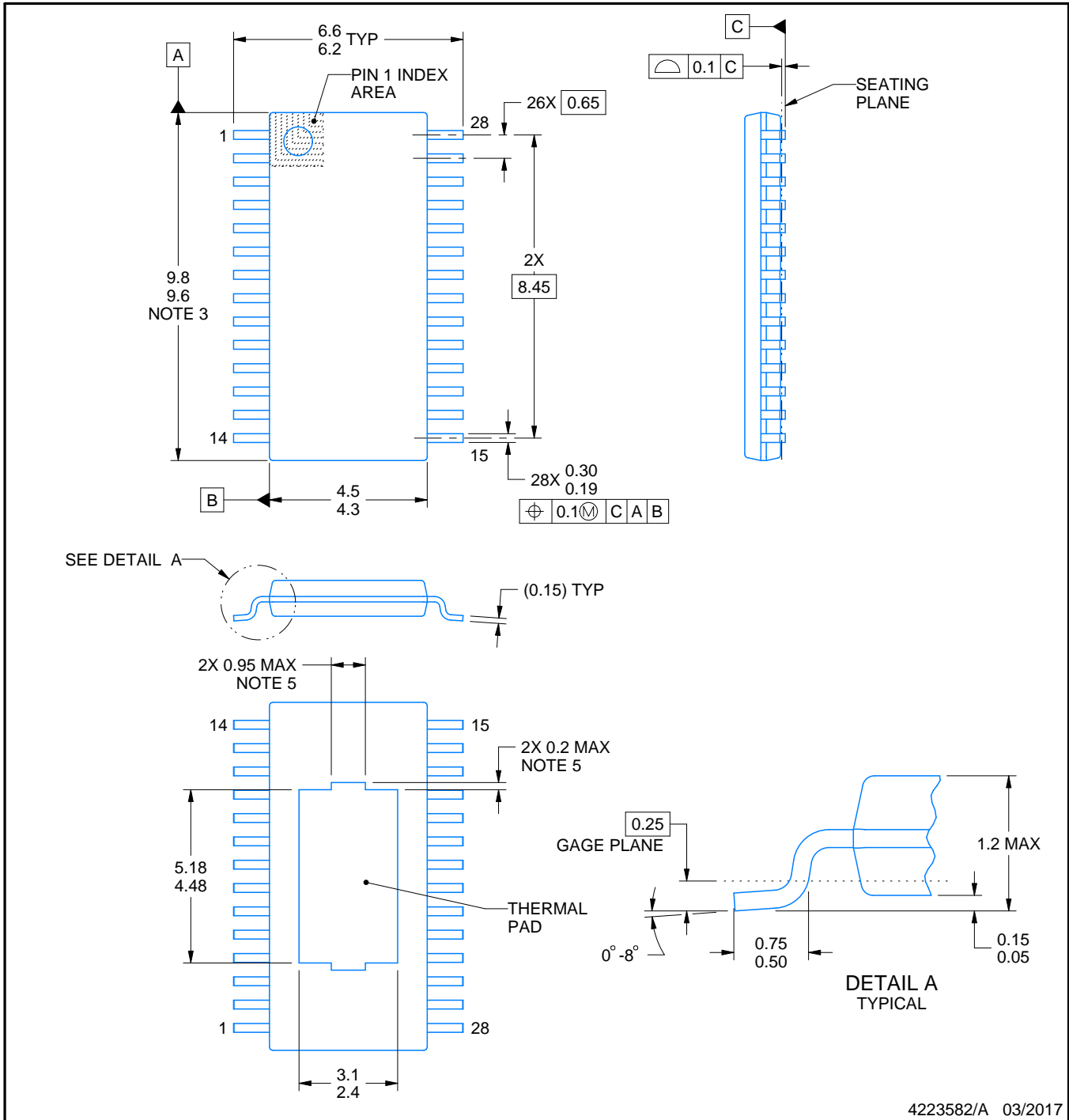
PWP0028C



PACKAGE OUTLINE

PowerPAD™ TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



4223582/A 03/2017

NOTES:

PowerPAD is a trademark of Texas Instruments.

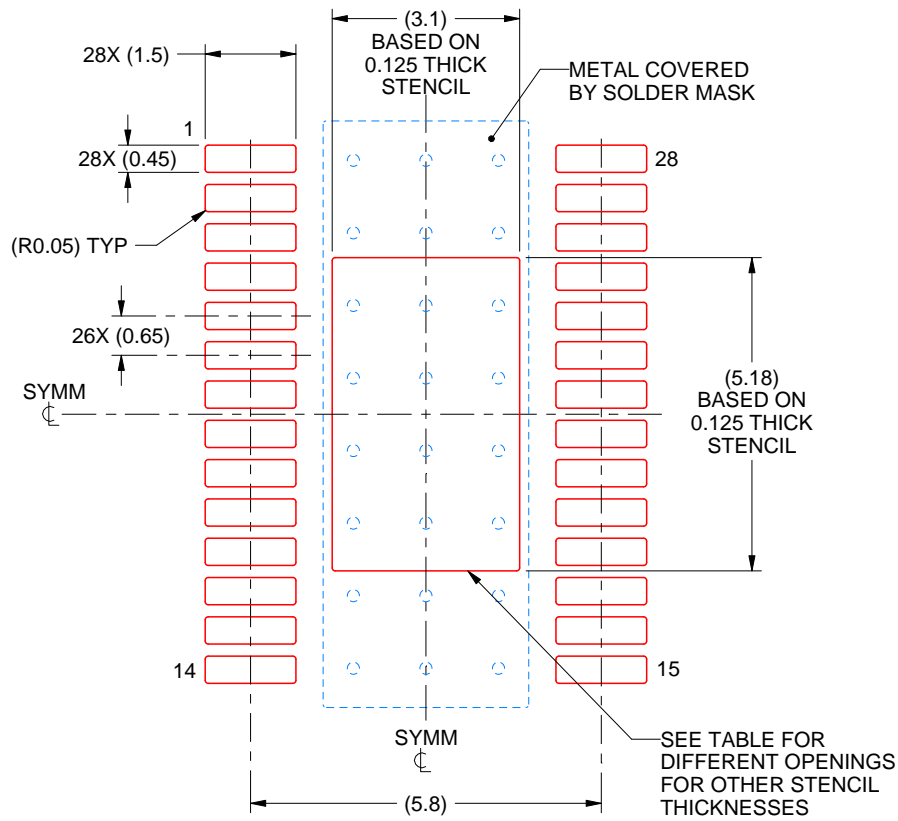
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. Reference JEDEC registration MO-153.
5. Features may differ or may not be present.

EXAMPLE STENCIL DESIGN

PWP0028C

PowerPAD™ TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
 BASED ON 0.125 mm THICK STENCIL
 SCALE: 8X

STENCIL THICKNESS	SOLDER STENCIL OPENING
0.1	3.47 X 5.79
0.125	3.10 X 5.18 (SHOWN)
0.15	2.83 X 4.73
0.175	2.62 X 4.38

4223582/A 03/2017

NOTES: (continued)

11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
12. Board assembly site may have different recommendations for stencil design.

重要声明和免责声明

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